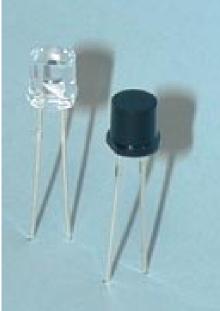
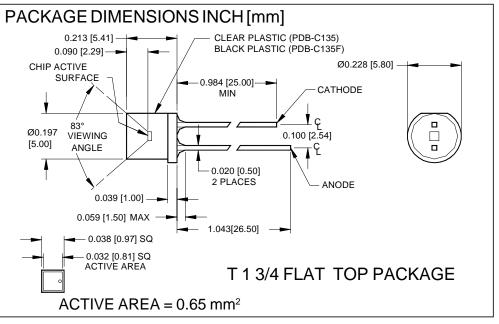
PHOTONIC si DETECTORS INC.



Silicon Photodiode, Blue Enhanced Photoconductive Type PDB-C135, with daylight filter Type PDB-C135F



FEATURES

- Flat top T 1 3/4
- High speed, 1 nS (tr)
- Low cost

DESCRIPTION: The **PDB-C135** detector is a 0.65 mm² planar pin photodiode packaged in a T 1 3/4,flat top, water clear plastic housing. Designed for high speed, low capacitance, photoconductive applications. The **PDB-C135F** includes a daylight filter.

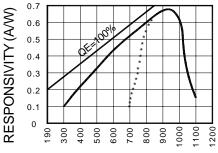
APPLICATIONS

- Smoke detectors
- Light pen detectors
- TV & VCR remotes

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS			
V _{BR}	Reverse Voltage		100	V			
T _{stg}	Storage Temperature	-40	+100	°C			
T _o	Operating Temperature Range	-40	+80	°C			
T _s	Soldering Temperature*		+260	°C			
Ι	Light Current		0.5	mA			

SPECTRAL RESPONSE



WAVELENGTH (nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS				
I _{sc}	Short Circuit Current	H = 100 fc, 2850 K	8	10		μ A				
I _D	Dark Current	H = 0, V _R = 10 V		2	10	nA				
R _{sh}	Shunt Resistance	H = 0, V _R = 10 mV	.5	5		GΩ				
TC R _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		%/°C				
CJ	Junction Capacitance	$H = 0, V_{R} = 10 V^{*}$		2	5	pF				
λrange	Spectral Application Range	(without daylight filter)**	400		1100	nm				
λρ	Spectral Response - Peak			950		nm				
V _{BR}	Breakdown Voltage	I = 10 μA	50	100		V				
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.5x10 ⁻¹³		W/ √ Hz				
tr	Response Time	$RL = 1 K\Omega V_R = 50 V$		5		nS				

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. *f = 1 MHz, ** daylight filter = 700 - 1100 nm [FORM NO. 100-PDB-C135 REV A]